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Applicants: Aratani et al. )  
Serial No.: 09/429,719 )  
Title: Thin Film Formation Use Sputtering ... )  
Atty. Docket No. 9792486-0010 (formerly P99,2247) )

) Examiner: R. McDonald

) FEB 8 2001

) Group Unit: 1753

GROUP 1700

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2/2/01

Response to First Office Action

In response to the First Office Action dated, 24 July 2000, the applicants respond as follows.

A. In the Claims:

1. (Amended) A method of forming a thin film comprising the step of: forming an AgPd alloy thin film using a sputtering target material, [wherein] the AgPd alloy thin film comprises Pd in an amount ranging from 0.5 to 4.9 atomic %; and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.

SNB B2 7. (Amended) A method of forming a thin film comprising the step of: forming an AgPdT<sub>x</sub> alloy thin film using a sputtering target material, [wherein] the AgPdT<sub>x</sub> alloy comprises Pd in an amount ranging from 0.1 to 1.5 atomic % and Ti in an amount ranging from 0.1 to 2.9 atomic %; and irradiating an information recording layer with a light beam having a wavelength of less than or equal to 800 nm.

R120 10 8. (New) The method of claim 1, wherein the wavelength is less than or equal to 650 nm.

R126 11 9. (New) The method of claim 2, wherein the wavelength is less than or equal to 650 nm.